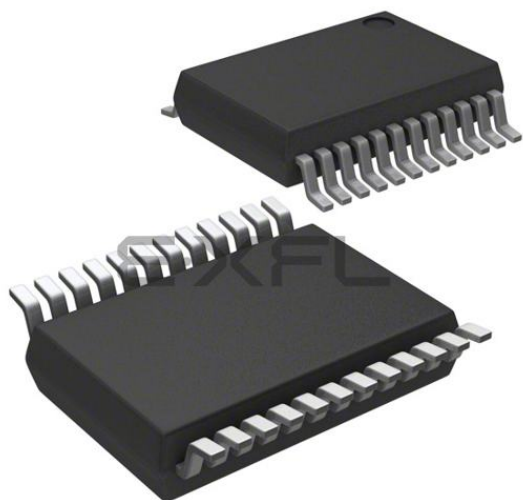




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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I ² C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	19
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 8x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	24-LSSOP (0.220", 5.60mm Width)
Supplier Device Package	24-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f213g4cnsp-u0

Table 1.2 Specifications for R8C/3GC Group (2)

Item	Function	Specification
Serial Interface	UART0	Clock synchronous serial I/O/UART
	UART2	Clock synchronous serial I/O/UART, I ² C mode (I ² C-bus), multiprocessor communication function
Synchronous Serial Communication Unit (SSU)		1 (shared with I ² C-bus)
I ² C bus		1 (shared with SSU)
LIN Module		Hardware LIN: 1 (timer RA, UART0)
A/D Converter		10-bit resolution × 8 channels, includes sample and hold function, with sweep mode
D/A Converter		8-bit resolution × 2 circuits
Comparator B		2 circuits
Flash Memory		• Programming and erasure voltage: VCC = 2.7 to 5.5 V • Programming and erasure endurance: 10,000 times (data flash) 1,000 times (program ROM) • Program security: ROM code protect, ID code check • Debug functions: On-chip debug, on-board flash rewrite function • Background operation (BGO) function
Operating Frequency/Supply Voltage		f(XIN) = 20 MHz (VCC = 2.7 to 5.5 V) f(XIN) = 5 MHz (VCC = 1.8 to 5.5 V)
Current Consumption		Typ. 6.5 mA (VCC = 5.0 V, f(XIN) = 20 MHz) Typ. 3.5 mA (VCC = 3.0 V, f(XIN) = 10 MHz) Typ. 3.5 μA (VCC = 3.0 V, wait mode (f(XCIN) = 32 kHz)) Typ. 2.0 μA (VCC = 3.0 V, stop mode)
Operating Ambient Temperature		-20 to 85°C (N version) -40 to 85°C (D version) ⁽¹⁾
Package		24-pin HWQFN Package code: PWQN0024KC-A 24-pin LSSOP Package code: PLSP0024JB-A (previous code: 24P2F-A)

Note:

1. Specify the D version if D version functions are to be used.

1.3 Block Diagram

Figure 1.2 shows a Block Diagram.

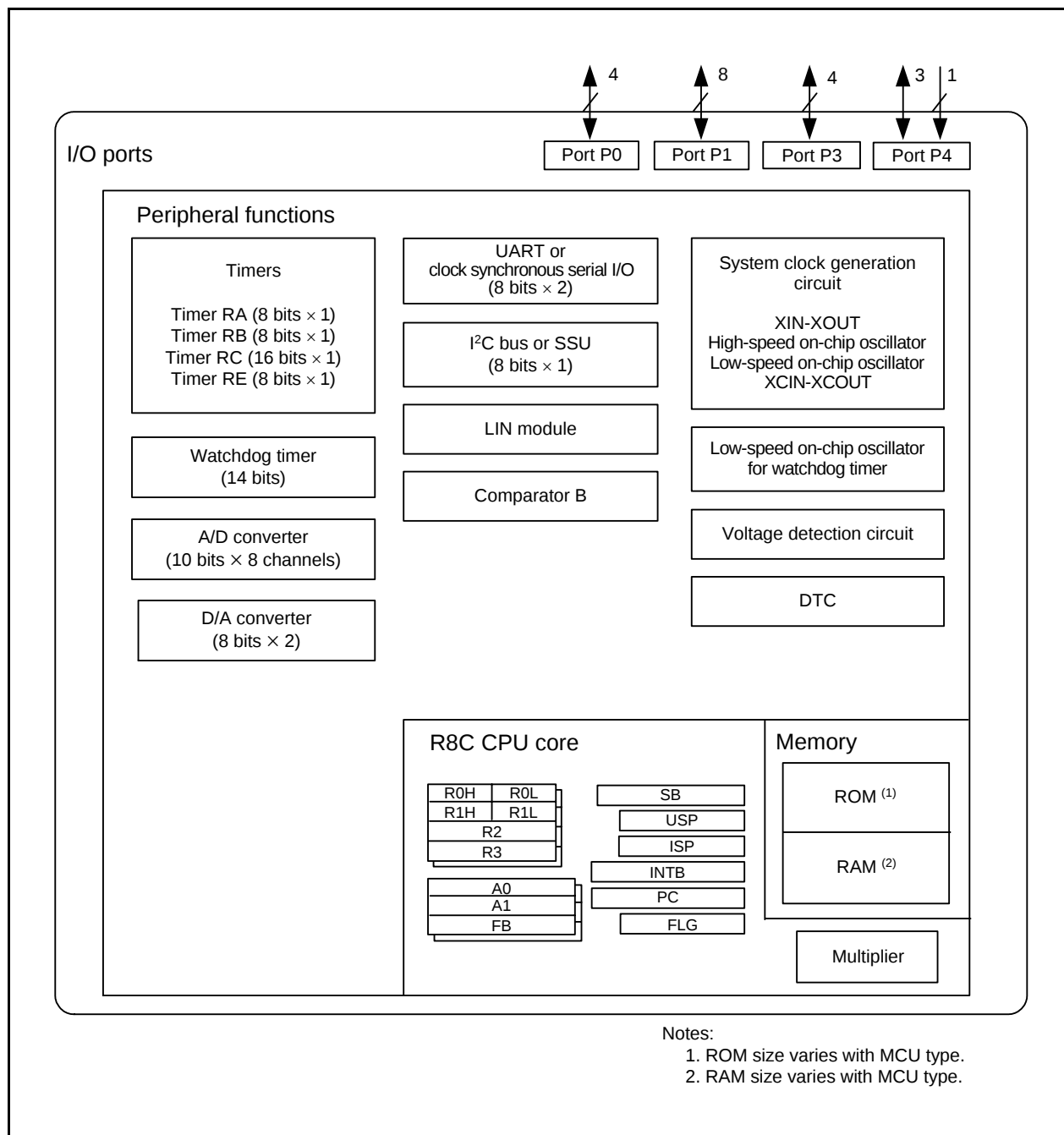


Figure 1.2 Block Diagram

1.4 Pin Assignment

Figure 1.3 shows Pin Assignment (Top View) of PWQN0024KC-A Package. Table 1.4 outlines the Pin Name Information by Pin Number.

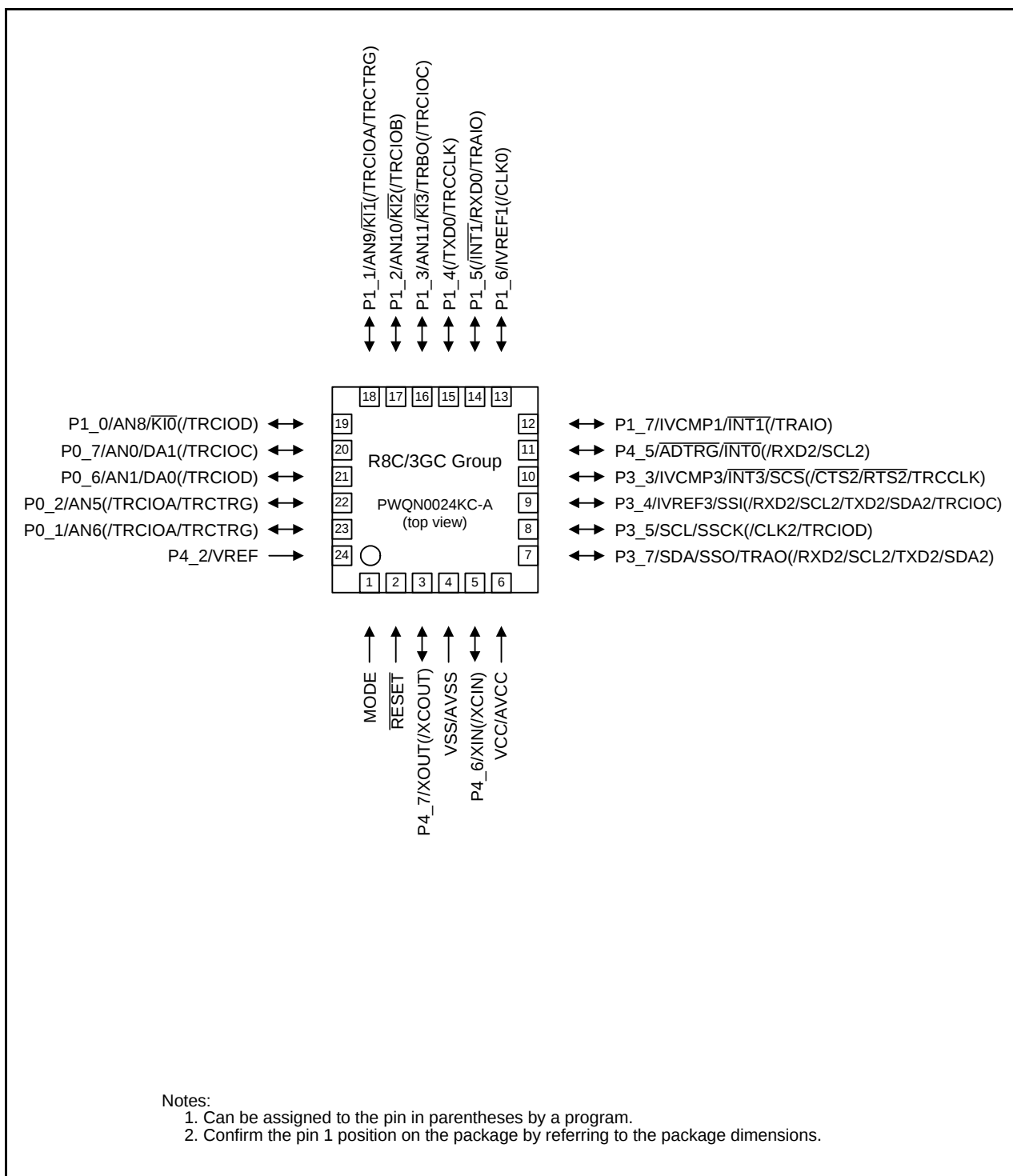


Figure 1.3 Pin Assignment (Top View) of PWQN0024KC-A Package

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU Registers. The CPU contains 13 registers. R0, R1, R2, R3, A0, A1, and FB configure a register bank. There are two sets of register bank.

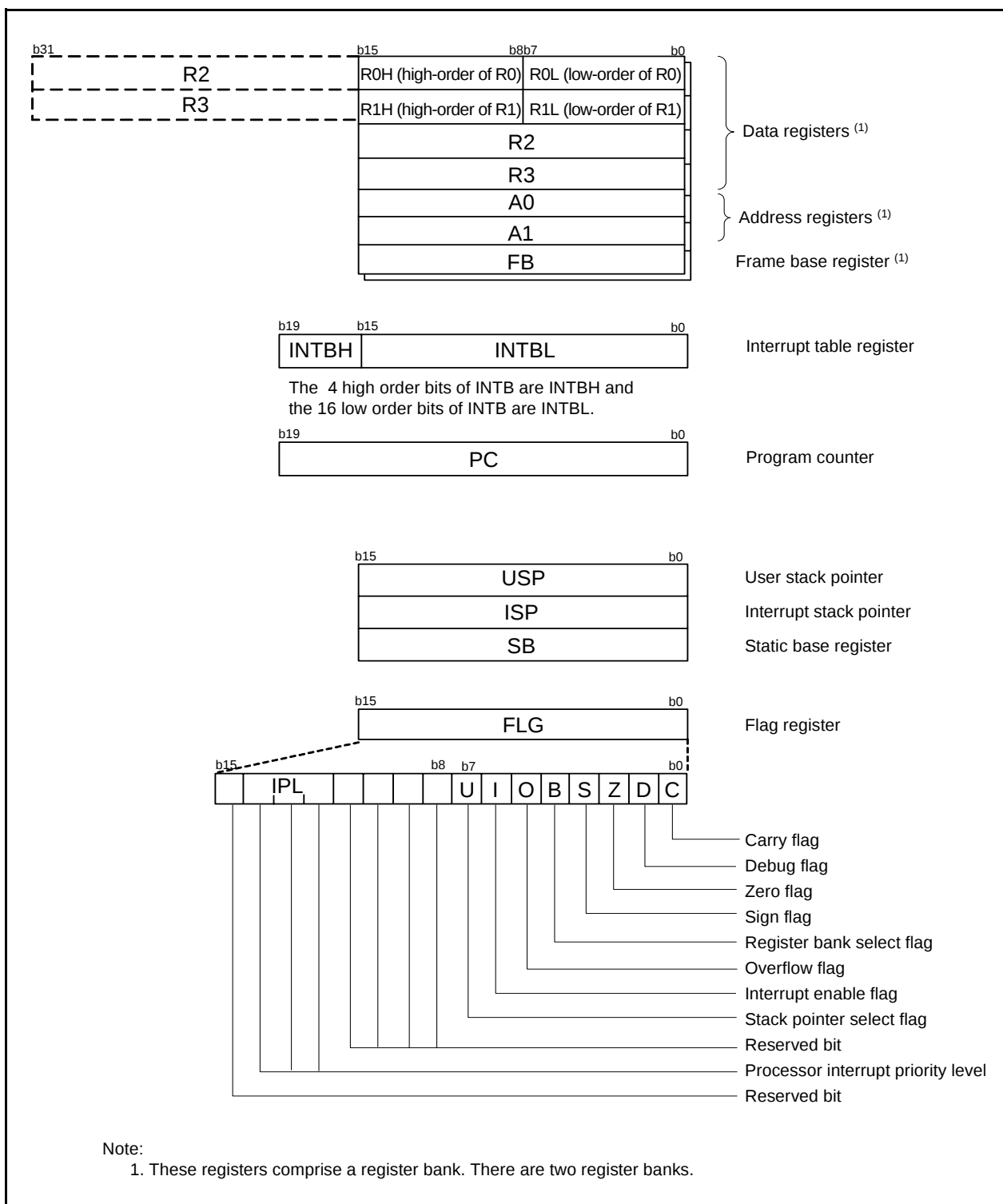


Figure 2.1 CPU Registers

2.1 Data Registers (R0, R1, R2, and R3)

R0 is a 16-bit register for transfer, arithmetic, and logic operations. The same applies to R1 to R3. R0 can be split into high-order bits (R0H) and low-order bits (R0L) to be used separately as 8-bit data registers. R1H and R1L are analogous to R0H and R0L. R2 can be combined with R0 and used as a 32-bit data register (R2R0). R3R1 is analogous to R2R0.

2.2 Address Registers (A0 and A1)

A0 is a 16-bit register for address register indirect addressing and address register relative addressing. It is also used for transfer, arithmetic, and logic operations. A1 is analogous to A0. A1 can be combined with A0 and as a 32-bit address register (A1A0).

2.3 Frame Base Register (FB)

FB is a 16-bit register for FB relative addressing.

2.4 Interrupt Table Register (INTB)

INTB is a 20-bit register that indicates the starting address of an interrupt vector table.

2.5 Program Counter (PC)

PC is 20 bits wide and indicates the address of the next instruction to be executed.

2.6 User Stack Pointer (USP) and Interrupt Stack Pointer (ISP)

The stack pointers (SP), USP and ISP, are each 16 bits wide. The U flag of FLG is used to switch between USP and ISP.

2.7 Static Base Register (SB)

SB is a 16-bit register for SB relative addressing.

2.8 Flag Register (FLG)

FLG is an 11-bit register indicating the CPU state.

2.8.1 Carry Flag (C)

The C flag retains carry, borrow, or shift-out bits that have been generated by the arithmetic and logic unit.

2.8.2 Debug Flag (D)

The D flag is for debugging only. Set it to 0.

2.8.3 Zero Flag (Z)

The Z flag is set to 1 when an arithmetic operation results in 0; otherwise to 0.

2.8.4 Sign Flag (S)

The S flag is set to 1 when an arithmetic operation results in a negative value; otherwise to 0.

2.8.5 Register Bank Select Flag (B)

Register bank 0 is selected when the B flag is 0. Register bank 1 is selected when this flag is set to 1.

2.8.6 Overflow Flag (O)

The O flag is set to 1 when an operation results in an overflow; otherwise to 0.

Table 4.2 SFR Information (2) ⁽¹⁾

Address	Register	Symbol	After Reset
003Ah	Voltage Monitor 2 Circuit Control Register	VW2C	10000010b
003Bh			
003Ch			
003Dh			
003Eh			
003Fh			
0040h			
0041h	Flash Memory Ready Interrupt Control Register	FMRDYIC	XXXXX000b
0042h			
0043h			
0044h			
0045h			
0046h			
0047h	Timer RC Interrupt Control Register	TRCIC	XXXXX000b
0048h			
0049h			
004Ah	Timer RE Interrupt Control Register	TREIC	XXXXX000b
004Bh	UART2 Transmit Interrupt Control Register	S2TIC	XXXXX000b
004Ch	UART2 Receive Interrupt Control Register	S2RIC	XXXXX000b
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh	A/D Conversion Interrupt Control Register	ADIC	XXXXX000b
004Fh	SSU Interrupt Control Register / IIC bus Interrupt Control Register ⁽²⁾	SSUIC / IICIC	XXXXX000b
0050h			
0051h	UART0 Transmit Interrupt Control Register	S0TIC	XXXXX000b
0052h	UART0 Receive Interrupt Control Register	S0RIC	XXXXX000b
0053h			
0054h			
0055h			
0056h	Timer RA Interrupt Control Register	TRAIC	XXXXX000b
0057h			
0058h	Timer RB Interrupt Control Register	TRBIC	XXXXX000b
0059h	INT1 Interrupt Control Register	INT1IC	XX00X000b
005Ah	INT3 Interrupt Control Register	INT3IC	XX00X000b
005Bh			
005Ch			
005Dh	INT0 Interrupt Control Register	INT0IC	XX00X000b
005Eh	UART2 Bus Collision Detection Interrupt Control Register	U2BCNIC	XXXXX000b
005Fh			
0060h			
0061h			
0062h			
0063h			
0064h			
0065h			
0066h			
0067h			
0068h			
0069h			
006Ah			
006Bh			
006Ch			
006Dh			
006Eh			
006Fh			
0070h			
0071h			
0072h	Voltage Monitor 1 Interrupt Control Register	VCMP1IC	XXXXX000b
0073h	Voltage Monitor 2 Interrupt Control Register	VCMP2IC	XXXXX000b
0074h			
0075h			
0076h			
0077h			
0078h			
0079h			
007Ah			
007Bh			
007Ch			
007Dh			
007Eh			
007Fh			

X: Undefined

Notes:

1. The blank areas are reserved and cannot be accessed by users.
2. Selectable by the IICSEL bit in the SSUICSR register.

Table 4.6 SFR Information (6) (1)

Address	Register	Symbol	After Reset
0140h			
0141h			
0142h			
0143h			
0144h			
0145h			
0146h			
0147h			
0148h			
0149h			
014Ah			
014Bh			
014Ch			
014Dh			
014Eh			
014Fh			
0150h			
0151h			
0152h			
0153h			
0154h			
0155h			
0156h			
0157h			
0158h			
0159h			
015Ah			
015Bh			
015Ch			
015Dh			
015Eh			
015Fh			
0160h			
0161h			
0162h			
0163h			
0164h			
0165h			
0166h			
0167h			
0168h			
0169h			
016Ah			
016Bh			
016Ch			
016Dh			
016Eh			
016Fh			
0170h			
0171h			
0172h			
0173h			
0174h			
0175h			
0176h			
0177h			
0178h			
0179h			
017Ah			
017Bh			
017Ch			
017Dh			
017Eh			
017Fh			

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 4.10 SFR Information (10) ⁽¹⁾

Address	Register	Symbol	After Reset
2C70h	DTC Control Data 6	DTCD6	XXh
2C71h			XXh
2C72h			XXh
2C73h			XXh
2C74h			XXh
2C75h			XXh
2C76h			XXh
2C77h			XXh
2C78h	DTC Control Data 7	DTCD7	XXh
2C79h			XXh
2C7Ah			XXh
2C7Bh			XXh
2C7Ch			XXh
2C7Dh			XXh
2C7Eh			XXh
2C7Fh			XXh
2C80h	DTC Control Data 8	DTCD8	XXh
2C81h			XXh
2C82h			XXh
2C83h			XXh
2C84h			XXh
2C85h			XXh
2C86h			XXh
2C87h			XXh
2C88h	DTC Control Data 9	DTCD9	XXh
2C89h			XXh
2C8Ah			XXh
2C8Bh			XXh
2C8Ch			XXh
2C8Dh			XXh
2C8Eh			XXh
2C8Fh			XXh
2C90h	DTC Control Data 10	DTCD10	XXh
2C91h			XXh
2C92h			XXh
2C93h			XXh
2C94h			XXh
2C95h			XXh
2C96h			XXh
2C97h			XXh
2C98h	DTC Control Data 11	DTCD11	XXh
2C99h			XXh
2C9Ah			XXh
2C9Bh			XXh
2C9Ch			XXh
2C9Dh			XXh
2C9Eh			XXh
2C9Fh			XXh
2CA0h	DTC Control Data 12	DTCD12	XXh
2CA1h			XXh
2CA2h			XXh
2CA3h			XXh
2CA4h			XXh
2CA5h			XXh
2CA6h			XXh
2CA7h			XXh
2CA8h	DTC Control Data 13	DTCD13	XXh
2CA9h			XXh
2CAAh			XXh
2CABh			XXh
2CACH			XXh
2CADh			XXh
2CAEh			XXh
2CAFh			XXh

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 5.2 Recommended Operating Conditions

Symbol	Parameter				Conditions	Standard			Unit
						Min.	Typ.	Max.	
Vcc/AVcc	Supply voltage					1.8	–	5.5	V
Vss/AVss	Supply voltage					–	0	–	V
VIH	Input “H” voltage	Other than CMOS input				0.8 Vcc	–	Vcc	V
		CMOS input	Input level switching function (I/O port)	Input level selection: 0.35 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0.5 Vcc	–	Vcc	V
					2.7 V ≤ Vcc < 4.0 V	0.55 Vcc	–	Vcc	V
					1.8 V ≤ Vcc < 2.7 V	0.65 Vcc	–	Vcc	V
			Input level selection: 0.5 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0.65 Vcc	–	Vcc	V	
				2.7 V ≤ Vcc < 4.0 V	0.7 Vcc	–	Vcc	V	
				1.8 V ≤ Vcc < 2.7 V	0.8 Vcc	–	Vcc	V	
				Input level selection: 0.7 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0.85 Vcc	–	Vcc	V
					2.7 V ≤ Vcc < 4.0 V	0.85 Vcc	–	Vcc	V
					1.8 V ≤ Vcc < 2.7 V	0.85 Vcc	–	Vcc	V
	External clock input (XOUT)				1.2	–	Vcc	V	
VIL	Input “L” voltage	Other than CMOS input				0	–	0.2 Vcc	V
		CMOS input	Input level switching function (I/O port)	Input level selection: 0.35 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0	–	0.2 Vcc	V
					2.7 V ≤ Vcc < 4.0 V	0	–	0.2 Vcc	V
					1.8 V ≤ Vcc < 2.7 V	0	–	0.2 Vcc	V
			Input level selection: 0.5 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0	–	0.4 Vcc	V	
				2.7 V ≤ Vcc < 4.0 V	0	–	0.3 Vcc	V	
				1.8 V ≤ Vcc < 2.7 V	0	–	0.2 Vcc	V	
				Input level selection: 0.7 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0	–	0.55 Vcc	V
					2.7 V ≤ Vcc < 4.0 V	0	–	0.45 Vcc	V
					1.8 V ≤ Vcc < 2.7 V	0	–	0.35 Vcc	V
	External clock input (XOUT)				0	–	0.4	V	
IOH(sum)	Peak sum output “H” current	Sum of all pins IOH(peak)				–	–	–160	mA
IOH(sum)	Average sum output “H” current	Sum of all pins IOH(avg)				–	–	–80	mA
IOH(peak)	Peak output “H” current	Drive capacity Low				–	–	–10	mA
		Drive capacity High				–	–	–40	mA
IOH(avg)	Average output “H” current	Drive capacity Low				–	–	–5	mA
		Drive capacity High				–	–	–20	mA
IOL(sum)	Peak sum output “L” current	Sum of all pins IOL(peak)				–	–	160	mA
IOL(sum)	Average sum output “L” current	Sum of all pins IOL(avg)				–	–	80	mA
IOL(peak)	Peak output “L” current	Drive capacity Low				–	–	10	mA
		Drive capacity High				–	–	40	mA
IOL(avg)	Average output “L” current	Drive capacity Low				–	–	5	mA
		Drive capacity High				–	–	20	mA
f(XIN)	XIN clock input oscillation frequency				2.7 V ≤ Vcc ≤ 5.5 V	–	–	20	MHz
					1.8 V ≤ Vcc < 2.7 V	–	–	5	MHz
f(XCIN)	XCIN clock input oscillation frequency				1.8 V ≤ Vcc ≤ 5.5 V	–	32.768	50	kHz
fOCO40M	When used as the count source for timer RC ⁽³⁾				2.7 V ≤ Vcc ≤ 5.5 V	32	–	40	MHz
fOCO-F	fOCO-F frequency				2.7 V ≤ Vcc ≤ 5.5 V	–	–	20	MHz
					1.8 V ≤ Vcc < 2.7 V	–	–	5	MHz
–	System clock frequency				2.7 V ≤ Vcc ≤ 5.5 V	–	–	20	MHz
					1.8 V ≤ Vcc < 2.7 V	–	–	5	MHz
f(BCLK)	CPU clock frequency				2.7 V ≤ Vcc ≤ 5.5 V	–	–	20	MHz
					1.8 V ≤ Vcc < 2.7 V	–	–	5	MHz

Notes:

1. V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.
3. f_{OCO40M} can be used as the count source for timer RC in the range of V_{CC} = 2.7 V to 5.5V.

Table 5.4 D/A Converter Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
—	Resolution		—	—	8	Bit
—	Absolute accuracy		—	—	2.5	LSB
t_{su}	Setup time		—	—	3	μs
R_o	Output resistor		—	6	—	$k\Omega$
I_{vref}	Reference power input current	(Note 2)	—	—	1.5	mA

Notes:

1. $V_{CC}/AV_{CC} = V_{ref} = 2.7$ to 5.5 V and $T_{opr} = -20$ to $85^{\circ}C$ (N version) / -40 to $85^{\circ}C$ (D version), unless otherwise specified.
2. This applies when one D/A converter is used and the value of the DA_i register ($i = 0$ or 1) for the unused D/A converter is $00h$. The resistor ladder of the A/D converter is not included.

Table 5.5 Comparator B Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{ref}	$IVREF1$, $IVREF3$ input reference voltage		0	—	$V_{CC} - 1.4$	V
V_i	$IVCMP1$, $IVCMP3$ input voltage		-0.3	—	$V_{CC} + 0.3$	V
—	Offset		—	5	100	mV
t_d	Comparator output delay time ⁽²⁾	$V_i = V_{ref} \pm 100$ mV	—	0.1	—	μs
I_{CMP}	Comparator operating current	$V_{CC} = 5.0$ V	—	17.5	—	μA

Notes:

1. $V_{CC} = 2.7$ to 5.5 V, $T_{opr} = -20$ to $85^{\circ}C$ (N version) / -40 to $85^{\circ}C$ (D version), unless otherwise specified.
2. When the digital filter is disabled.

Table 5.6 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance ⁽²⁾		1,000 ⁽³⁾	—	—	times
—	Byte program time		—	80	500	μs
—	Block erase time		—	0.3	—	s
t _d (SR-SUS)	Time delay from suspend request until suspend		—	—	5+CPU clock × 3 cycles	ms
—	Interval from erase start/restart until following suspend request		0	—	—	μs
—	Time from suspend until erase restart		—	—	30+CPU clock × 1 cycle	μs
t _d (CMDRST-READY)	Time from when command is forcibly terminated until reading is enabled		—	—	30+CPU clock × 1 cycle	μs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		0	—	60	°C
—	Data hold time ⁽⁷⁾	Ambient temperature = 55°C	20	—	—	year

Notes:

1. V_{CC} = 2.7 to 5.5 V and T_{opr} = 0 to 60°C, unless otherwise specified.

2. Definition of programming/erasure endurance

The programming and erasure endurance is defined on a per-block basis.

If the programming and erasure endurance is n (n = 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.

However, the same address must not be programmed more than once per erase operation (overwriting prohibited).

3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).

4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.

5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.

6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.

7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.10 Voltage Detection 2 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
Vdet2	Voltage detection level Vdet2_0	At the falling of Vcc	3.70	4.00	4.30	V
—	Hysteresis width at the rising of Vcc in voltage detection 2 circuit		—	0.10	—	V
—	Voltage detection 2 circuit response time ⁽²⁾	At the falling of Vcc from 5 V to (Vdet2_0 – 0.1) V	—	20	150	μs
—	Voltage detection circuit self power consumption	VCA27 = 1, Vcc = 5.0 V	—	1.7	—	μA
td(E-A)	Waiting time until voltage detection circuit operation starts ⁽³⁾		—	—	100	μs

Notes:

1. The measurement condition is Vcc = 1.8 V to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes Vdet2.
3. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.

Table 5.11 Power-on Reset Circuit (2)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
trth	External power Vcc rise gradient	(1)	0	—	50,000	mV/msec

Notes:

1. The measurement condition is T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. To use the power-on reset function, enable voltage monitor 0 reset by setting the LVDAS bit in the OFS register to 0.

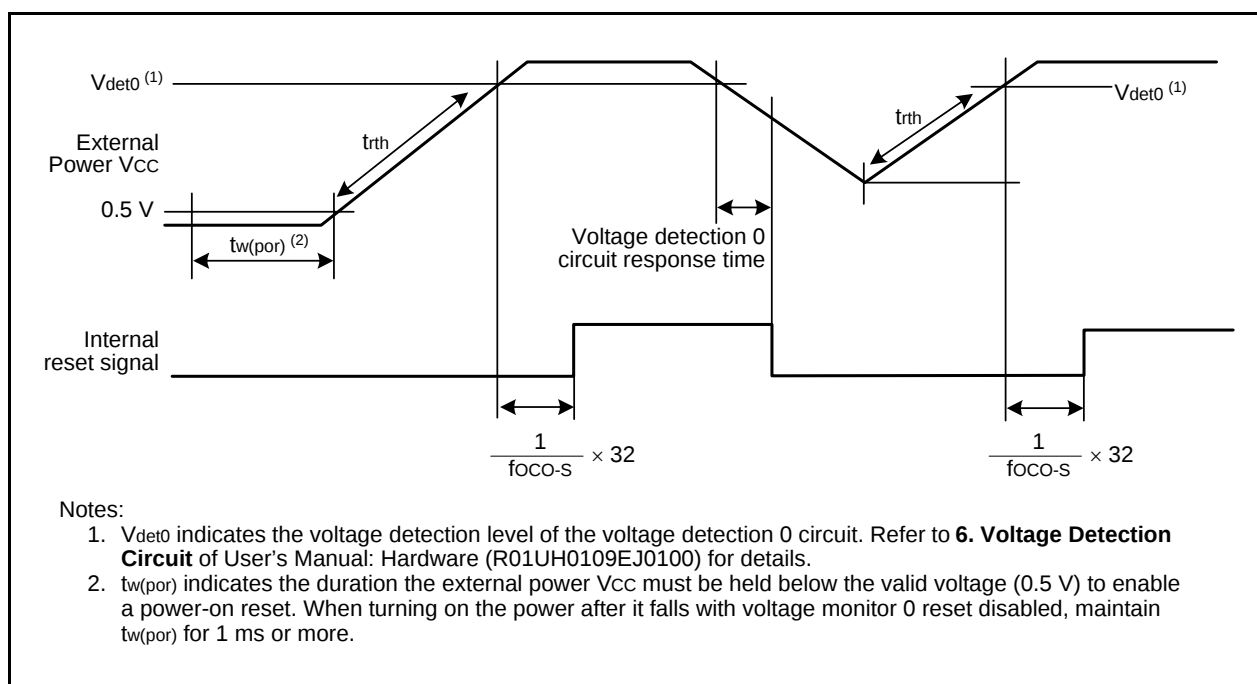
**Figure 5.3 Power-on Reset Circuit Electrical Characteristics**

Table 5.15 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t _{d(P-R)}	Time for internal power supply stabilization during power-on ⁽²⁾		–	–	2,000	μs

Notes:

1. The measurement condition is V_{CC} = 1.8 to 5.5 V and T_{opr} = 25°C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.

Table 5.16 Timing Requirements of Synchronous Serial Communication Unit (SSU) ⁽¹⁾

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
t _{SUCYC}	SSCK clock cycle time			4	–	–	t _{CYC} ⁽²⁾
t _{HI}	SSCK clock "H" width			0.4	–	0.6	t _{SUCYC}
t _{LO}	SSCK clock "L" width			0.4	–	0.6	t _{SUCYC}
t _{RISE}	SSCK clock rising time	Master		–	–	1	t _{CYC} ⁽²⁾
		Slave		–	–	1	μs
t _{FALL}	SSCK clock falling time	Master		–	–	1	t _{CYC} ⁽²⁾
		Slave		–	–	1	μs
t _{SU}	SSO, SSI data input setup time			100	–	–	ns
t _H	SSO, SSI data input hold time			1	–	–	t _{CYC} ⁽²⁾
t _{LEAD}	$\overline{\text{SCS}}$ setup time	Slave		1t _{CYC} + 50	–	–	ns
t _{LAG}	$\overline{\text{SCS}}$ hold time	Slave		1t _{CYC} + 50	–	–	ns
t _{OD}	SSO, SSI data output delay time			–	–	1	t _{CYC} ⁽²⁾
t _{SA}	SSI slave access time		2.7 V ≤ V _{CC} ≤ 5.5 V	–	–	1.5t _{CYC} + 100	ns
			1.8 V ≤ V _{CC} < 2.7 V	–	–	1.5t _{CYC} + 200	ns
t _{OR}	SSI slave out open time		2.7 V ≤ V _{CC} ≤ 5.5 V	–	–	1.5t _{CYC} + 100	ns
			1.8 V ≤ V _{CC} < 2.7 V	–	–	1.5t _{CYC} + 200	ns

Notes:

1. V_{CC} = 1.8 to 5.5 V, V_{SS} = 0 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. 1t_{CYC} = 1/f₁(s)

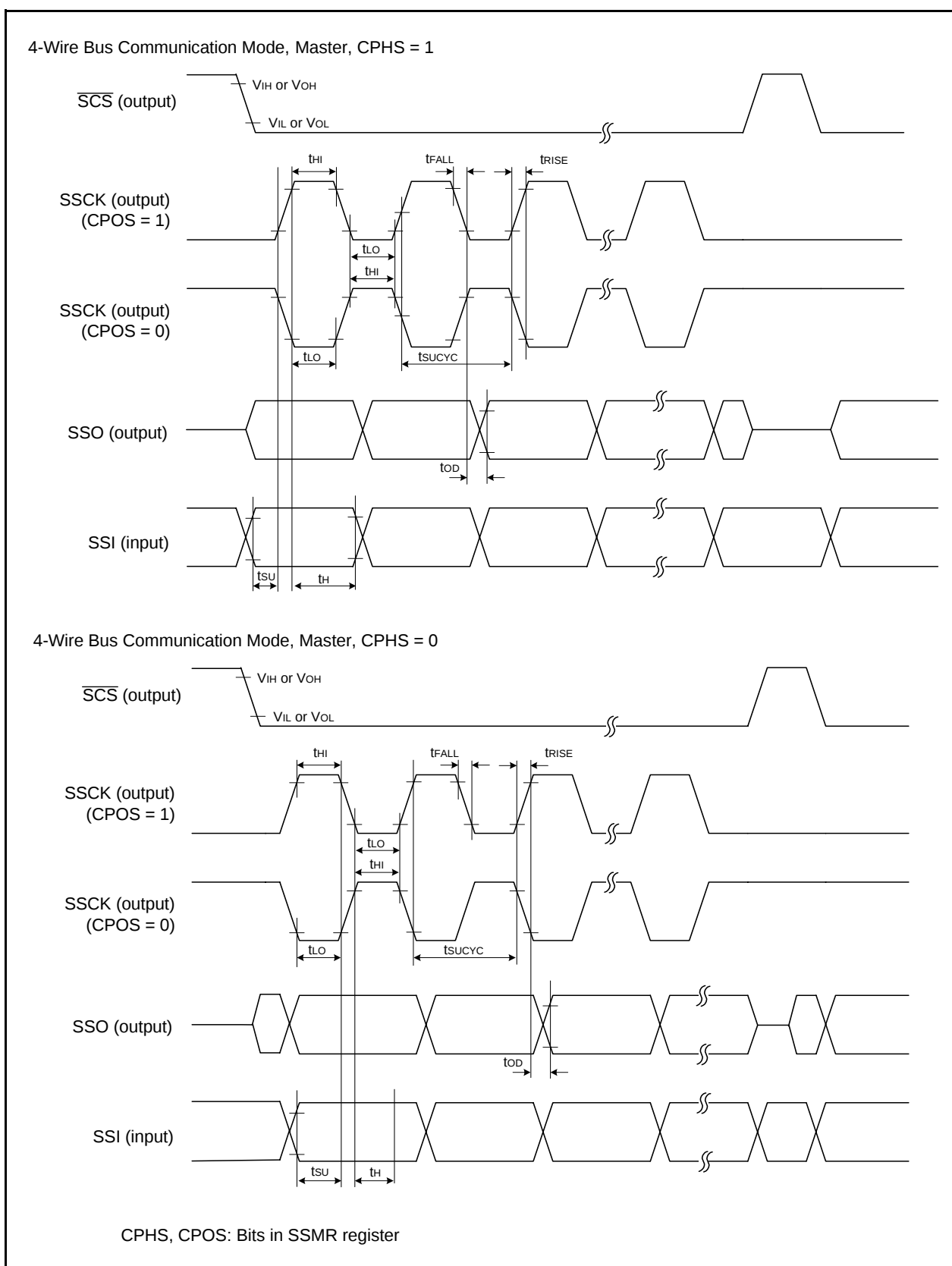


Figure 5.4 I/O Timing of Synchronous Serial Communication Unit (SSU) (Master)

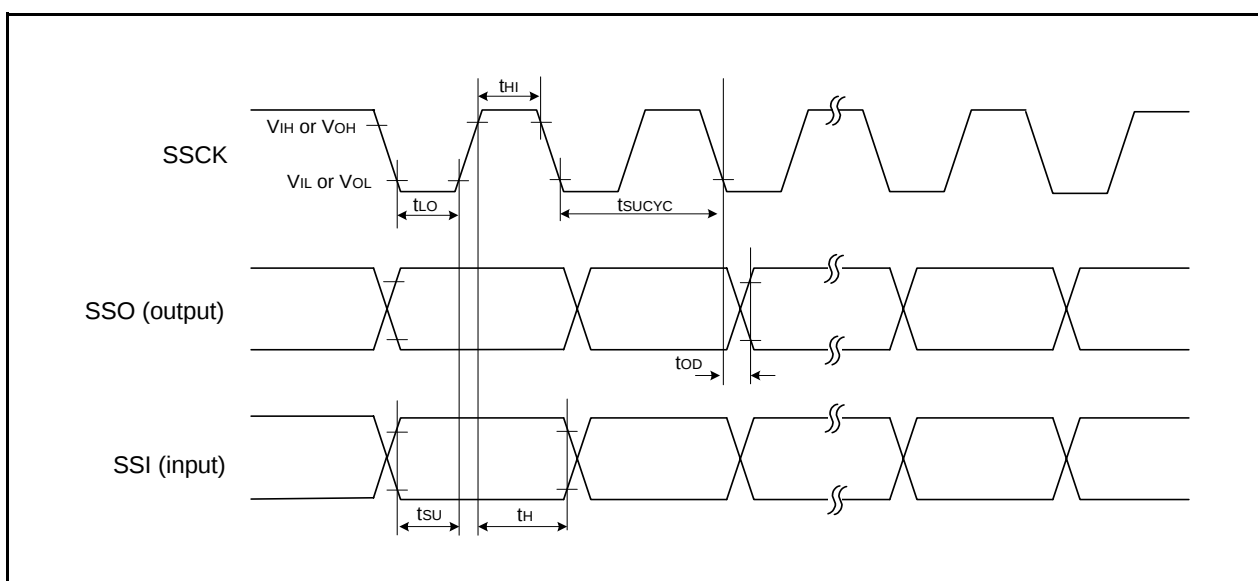


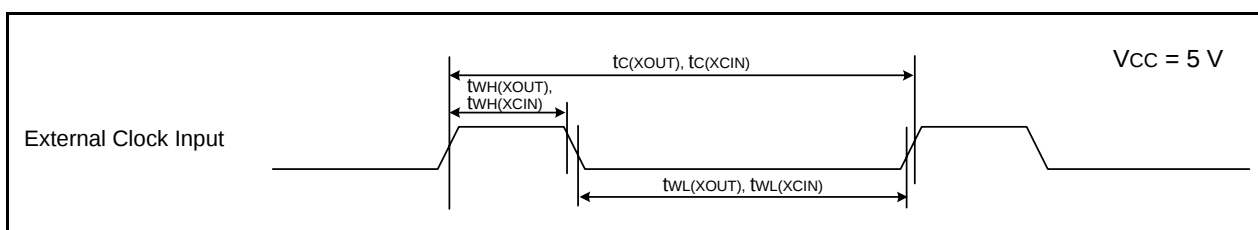
Figure 5.6 I/O Timing of Synchronous Serial Communication Unit (SSU) (Clock Synchronous Communication Mode)

Table 5.19 Electrical Characteristics (2) [$3.3\text{ V} \leq V_{CC} \leq 5.5\text{ V}$]
($T_{opr} = -20\text{ to }85^{\circ}\text{C}$ (N version) / $-40\text{ to }85^{\circ}\text{C}$ (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are Vss	High-speed clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	6.5	15	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	5.3	12.5	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	3.6	—	mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	3.0	—	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	2.2	—	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	1.5	—	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	—	7.0	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	3.0	—	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16, MSTIC = MSTTRD = MSTTRC = 1	—	1	—	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	—	90	400	μA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division, FMR27 = 1, VCA20 = 0	—	85	400	μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division, Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	—	47	—	μA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	—	15	100	μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	—	4	90	μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	—	3.5	—	μA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1, Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	2.0	5.0	μA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1, Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	5.0	—	μA

Timing Requirements**(Unless Otherwise Specified: $V_{CC} = 5\text{ V}$, $V_{SS} = 0\text{ V}$ at $T_{opr} = 25^\circ\text{C}$)****Table 5.20 External Clock Input (XOUT, XCIN)**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XOUT)}$	XOUT input cycle time	50	–	ns
$t_{WH(XOUT)}$	XOUT input “H” width	24	–	ns
$t_{WL(XOUT)}$	XOUT input “L” width	24	–	ns
$t_{c(XCIN)}$	XCIN input cycle time	14	–	μs
$t_{WH(XCIN)}$	XCIN input “H” width	7	–	μs
$t_{WL(XCIN)}$	XCIN input “L” width	7	–	μs

**Figure 5.8 External Clock Input Timing Diagram when $V_{CC} = 5\text{ V}$** **Table 5.21 TRAIO Input**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	100	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	40	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	40	–	ns

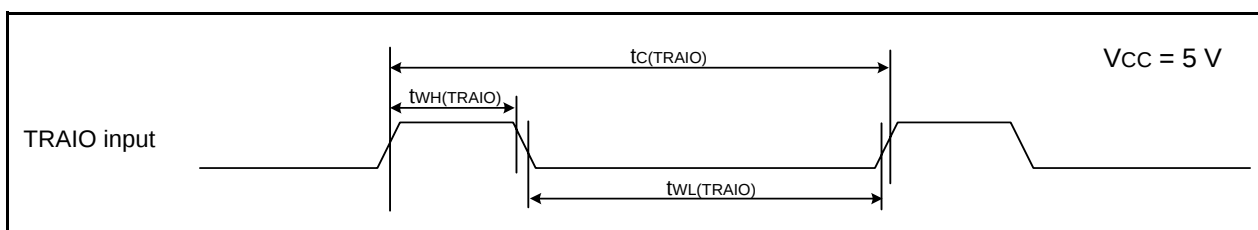
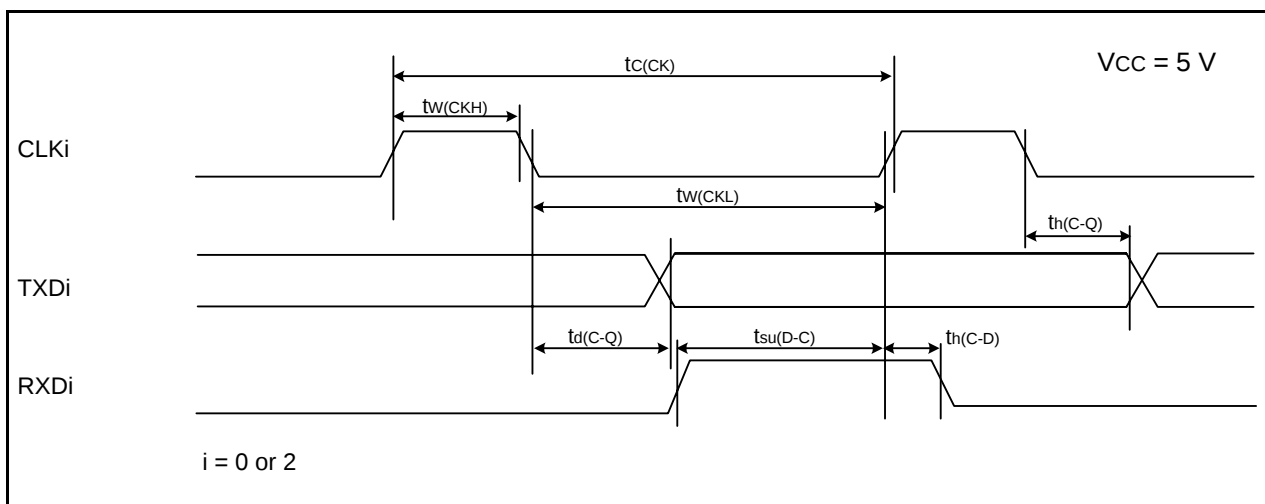
**Figure 5.9 TRAIO Input Timing Diagram when $V_{CC} = 5\text{ V}$**

Table 5.22 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	200	—	ns
$t_{w(CKH)}$	CLKi input "H" width	100	—	ns
$t_{w(CKL)}$	CLKi input "L" width	100	—	ns
$t_{d(C-Q)}$	TXDi output delay time	—	50	ns
$t_{h(C-Q)}$	TXDi hold time	0	—	ns
$t_{su(D-C)}$	RXDi input setup time	50	—	ns
$t_{h(C-D)}$	RXDi input hold time	90	—	ns

i = 0 or 2

**Figure 5.10 Serial Interface Timing Diagram when Vcc = 5 V****Table 5.23 External Interrupt $\overline{INTi}$ (i = 0, 1, 3) Input, Key Input Interrupt $\overline{Kli}$ (i = 0 to 3)**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{INTi}$ input "H" width, $\overline{Kli}$ input "H" width	250 ⁽¹⁾	—	ns
$t_{w(INL)}$	$\overline{INTi}$ input "L" width, $\overline{Kli}$ input "L" width	250 ⁽²⁾	—	ns

Notes:

1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

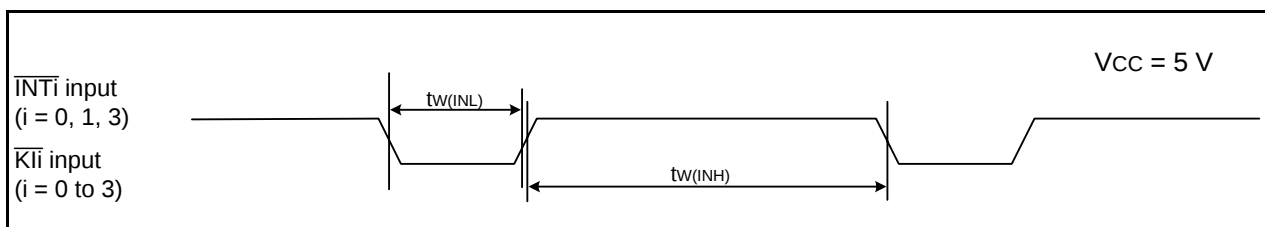
**Figure 5.11 Input Timing Diagram for External Interrupt $\overline{INTi}$ and Key Input Interrupt $\overline{Kli}$ when Vcc = 5 V**

Table 5.24 Electrical Characteristics (3) [$2.7\text{ V} \leq V_{CC} < 4.2\text{ V}$]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V _{OH}	Output "H" voltage	Other than XOUT	Drive capacity High	I _{OH} = –5 mA	V _{CC} – 0.5	–	V _{CC}	V
			Drive capacity Low	I _{OH} = –1 mA	V _{CC} – 0.5	–	V _{CC}	V
		XOUT		I _{OH} = –200 μ A	1.0	–	V _{CC}	V
V _{OL}	Output "L" voltage	Other than XOUT	Drive capacity High	I _{OL} = 5 mA	–	–	0.5	V
			Drive capacity Low	I _{OL} = 1 mA	–	–	0.5	V
		XOUT		I _{OL} = 200 μ A	–	–	0.5	V
V _{T+} –V _{T–}	Hysteresis	INT0, INT1, INT3, KI0, KI1, KI2, KI3, TRAIO, TRBO, TRCIOA, TRCIOB, TRCIOA, TRCIOB, TRCIOA, TRCIOB, TRCIOA, TRCIOB, TRCIOA, TRCIOB, ADTRG, RXD0, RXD2, CLK0, CLK2, SSI, SCL, SDA, SSO	V _{CC} = 3.0 V		0.1	0.4	–	V
		RESET	V _{CC} = 3.0 V		0.1	0.5	–	V
I _{IH}	Input "H" current		V _I = 3 V, V _{CC} = 3.0 V		–	–	4.0	μ A
I _{IL}	Input "L" current		V _I = 0 V, V _{CC} = 3.0 V		–	–	–4.0	μ A
R _{PULLUP}	Pull-up resistance		V _I = 0 V, V _{CC} = 3.0 V		42	84	168	k Ω
R _{FXIN}	Feedback resistance	XIN			–	0.3	–	M Ω
R _{FXCIN}	Feedback resistance	XCIN			–	8	–	M Ω
V _{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

Note:

1. $2.7\text{ V} \leq V_{CC} < 4.2\text{ V}$ and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), f(XIN) = 10 MHz, unless otherwise specified.

REVISION HISTORY	R8C/3GC Group Datasheet
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Rev.	Date	Description	
		Page	Summary
0.01	Oct. 30, 2009	—	First Edition issued
0.10	May 24, 2010	10	Table 1.6 XOUT: I → I/O
		28 to 54	"5. Electrical Characteristics" added
		55, 56	"Package Dimensions" revised
1.00	Oct 19, 2010	All	"Under development" deleted
		4	Table 1.3 QFN: D version deleted
		15	Figure 3.1 QFN: D version deleted
		31	Table 32.3 "tCONV", "tSAMP" revised
		37	Table 32.12 added, Table 32.13 revised

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